

**AMENDMENTS****In the Claims**

Claim 1 (currently amended): A nitride compound semiconductor light emitting device comprising:

a GaN substrate having a crystal orientation which is tilted away from its main plane orientation of a  $\langle 0001 \rangle$  direction by an angle which is equal to or greater than about 0.05 and which is equal to or less than about 2, and

a semiconductor multilayer structure formed on the GaN substrate,

wherein the semiconductor multilayer structure includes:

an acceptor doping layer containing a nitride compound semiconductor

comprising  $\text{Ga}_x\text{In}_y\text{Al}_{1-(x+y)}\text{N}$  (where  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq x+y \leq 1$ ), and

~~an active layer including a light emitting region, and wherein said active layer is formed evenly~~ containing a nitride compound semiconductor comprising  $\text{Ga}_x\text{In}_y\text{Al}_{1-(x+y)}\text{N}$  (where  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq x+y \leq 1$ ).

Claim 2 (cancelled)

Claim 3 (original): A nitride compound semiconductor light emitting device according to claim 1, wherein the GaN substrate has a crystal orientation which is tilted away from a  $\langle 0001 \rangle$  direction in a  $\langle 11-20 \rangle$  or  $\langle 1-100 \rangle$  direction.

Claim 4 (currently amended): A nitride compound semiconductor light emitting device according to claim 1, wherein the acceptor doping layer ~~layer~~ exhibits a p-type conductivity as grown.

Claim 5 (original): A nitride compound semiconductor light emitting device according to claim 1, wherein the GaN substrate and the active layer are formed so as to be apart from each other by a distance which is equal to or greater than about  $1\mu\text{m}$ .

Claim 6 (original): A nitride compound semiconductor light emitting device according to claim 1, wherein the active layer has a quantum well structure, and the active layer has an averaged surface roughness which is equal to or less than a thickness of a well layer in the quantum well structure.

Claim 7 (original): A nitride compound semiconductor light emitting device according to claim 1, wherein the active layer includes at least one well layer and at least one barrier layer.

Claim 8 (withdrawn): A method for producing a nitride compound semiconductor light emitting device, wherein a semiconductor multilayer structure including an active layer of a quantum well structure made by a nitride compound semiconductor and an acceptor doping layer is integrated on a GaN substrate having a crystal orientation which is tilted away from a  $\langle 0001 \rangle$  direction by an angle which is equal to or greater than about  $0.05^\circ$  and which is equal to or less than about  $2^\circ$ , the active layer including at least one barrier layer and at least one well layer, the method comprising the steps of:

stopping the growth of the active layer for a certain period of time after forming the well layer of the active layer including the at least one barrier layer and at least one well layer; and

stopping the growth of the nitride compound semiconductor for a certain period of time after forming the nitride compound semiconductor which contacts with the well layer and becomes the barrier layer having band-gap energy larger than that of the well layer.

Claim 9 (withdrawn): A method according to claim 8, wherein the predetermined length of a wait period is equal to or greater than about 1 second and is equal to or less than about 60 minutes.

Claim 10 (withdrawn): A method according to claim 8, further comprising:

supplying a carrier gas into the chamber, in which the GaN substrate is placed, during a wait period after at least one of the at least one well layer and the at least one barrier layer has been formed, the carrier gas comprising nitrogen as a main component.

Claim 11 (withdrawn): A method according to claim 8, further comprising:

supplying a carrier gas and a group V gas into a chamber, in which the GaN substrate is placed, during a wait period after at least one of the at least one well layer and the at least one barrier layer has been formed, the carrier gas comprising nitrogen as a main component.

Claim 12 (currently amended): A nitride compound semiconductor light emitting device ~~comprising:~~ according to claim 1, wherein said active layer is formed evenly with respect to a macroscopic view and a microscopic view relating to an order of thickness of the active layer  
~~— a GaN substrate having a crystal orientation which is tilted away from a <0001> direction by an angle which is equal to or greater than about 0.05° and which is equal to or less than about 2°, and~~

~~— a semiconductor multilayer structure formed on the GaN substrate,~~  
~~— wherein the semiconductor multilayer structure includes:~~  
~~— an acceptor doping layer containing a nitride compound semiconductor comprising  $\text{Ga}_x\text{In}_y\text{Al}_{1-(x+y)}\text{N}$  (where  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq x+y \leq 1$ , and~~  
~~— an active layer including a light emitting region, and~~  
~~wherein said acceptor doping layer is formed evenly.~~

Claim 13 (new): A nitride compound semiconductor light emitting device according to claim 1, wherein said acceptor doping layer is formed evenly with respect to a macroscopic view and a microscopic view relating to an order of thickness of the active layer.